**Product data sheet** 

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- Electrostatic Discharge (ESD) protection > 2 kV HBM
- AEC-Q101 qualified

## 3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	40	V
$V_{GS}$	gate-source voltage			-20	-	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	-	2.7	Α
Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 2.7 \text{ A}; T_j = 25 ^{\circ}\text{C}$		-	64	75	mΩ

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



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# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D I
2	S	source		
3	D	drain	1 2 TO-236AB (SOT23)	G S 017aaa255

# 6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PMV65ENEA	TO-236AB	plastic surface-mounted package; 3 leads	SOT23		

# 7. Marking

Table 4. Marking codes

Type number	Marking code [1]
PMV65ENEA	BT%

[1] % = placeholder for manufacturing site code

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# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

	Conditions		Min	Max	Unit
drain-source voltage	T <sub>j</sub> = 25 °C		-	40	V
gate-source voltage			-20	20	V
drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	2.7	Α
	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C	[1]	-	1.7	Α
peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10$ μs		-	11	Α
non-repetitive drain-source avalanche energy	$T_{j(init)}$ = 25 °C; $I_D$ = 0.3 A; DUT in avalanche (unclamped)		-	6.5	mJ
total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	490	mW
		[1]	-	940	mW
	T <sub>sp</sub> = 25 °C		-	6.25	W
junction temperature			-55	150	°C
ambient temperature			-55	150	°C
storage temperature			-65	150	°C
iode					
source current	T <sub>amb</sub> = 25 °C	[1]	-	0.91	Α
rating					,
electrostatic discharge voltage	НВМ	[3]	-	2000	V
	gate-source voltage  drain current  peak drain current  non-repetitive drain-source avalanche energy  total power dissipation  junction temperature ambient temperature storage temperature iode source current  rating				

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

<sup>[2]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

<sup>[3]</sup> Measured between all pins.

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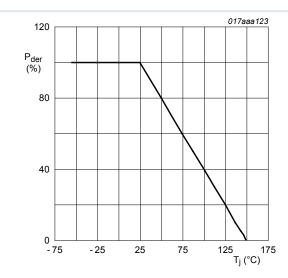


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

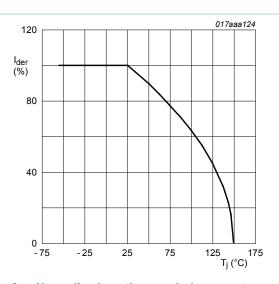


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

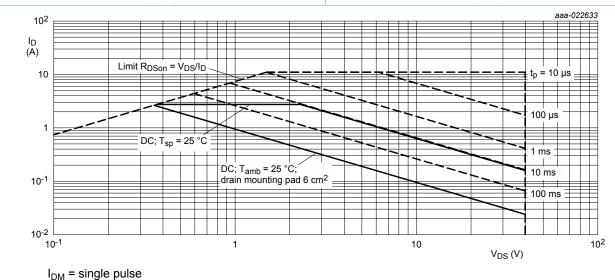


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance	in free air	[1]	-	221	254	K/W
	from junction to ambient		[2]	-	116	133	K/W

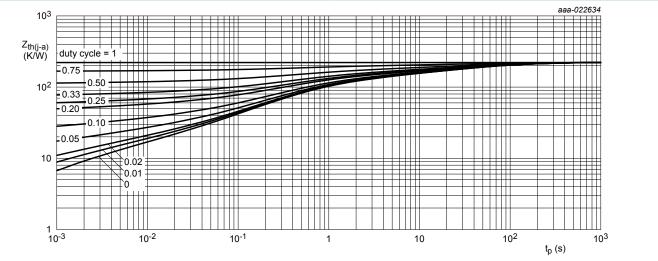
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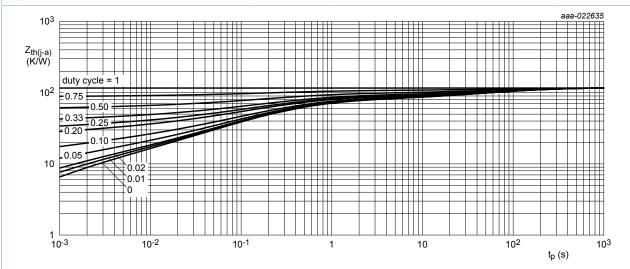
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		-	17	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 6 cm<sup>2</sup>

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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## 10. Characteristics

Table 7 Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D$ = 250 $\mu$ A; $V_{GS}$ = 0 V; $T_j$ = 25 °C	40	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1	1.6	2.5	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μA
		V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	5	μA
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-5	μA
		V <sub>GS</sub> = 4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
		$V_{GS}$ = -4.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-100	nA
R <sub>DSon</sub>	R <sub>DSon</sub> drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 2.7 A; $T_j$ = 25 °C	-	64	75	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 2.7 A; $T_j$ = 150 °C	-	109	136	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 2.4 A; T <sub>j</sub> = 25 °C	-	79	99	mΩ
9 <sub>fs</sub>	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 2 \text{ A}; T_j = 25 \text{ °C}$	-	10	-	S
$R_G$	gate resistance	T <sub>j</sub> = 25 °C; f = 1 MHz	-	11	-	Ω
Dynamic o	characteristics					
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 20 V; I <sub>D</sub> = 2.7 A; V <sub>GS</sub> = 10 V;	-	4.1	6	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C	-	0.5	-	nC
$Q_{GD}$	gate-drain charge		-	8.0	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 20 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	160	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	25	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	18	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 20 V; $I_{D}$ = 2.7 A; $V_{GS}$ = 10 V;	-	6	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	12	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	12	-	ns
t <sub>f</sub>	fall time		-	5	-	ns
Source-dr	ain diode			1	1	
$V_{SD}$	source-drain voltage	I <sub>S</sub> = 0.91 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-	8.0	1.2	V

10-3

### 40 V, N-channel Trench MOSFET

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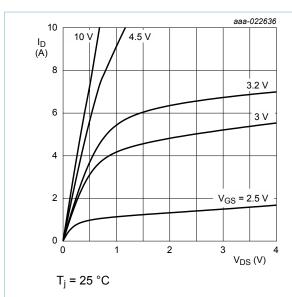


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

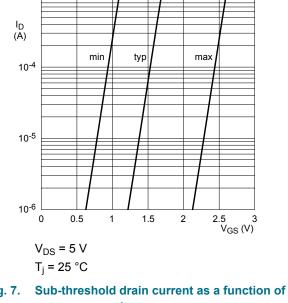
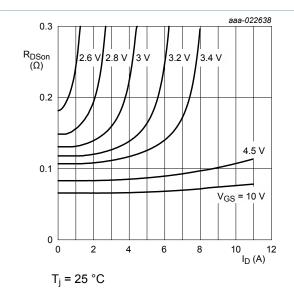


Fig. 7. gate-source voltage



Drain-source on-state resistance as a function of drain current; typical values

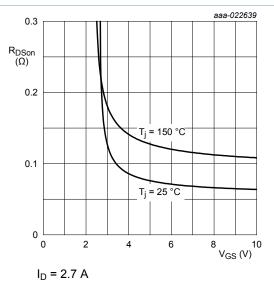


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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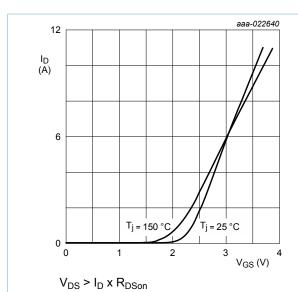


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

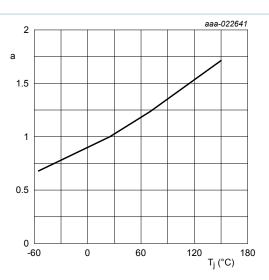


Fig. 11. Normalized drain-source on-state resistance as a function of ambient temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25 °C)}}$$

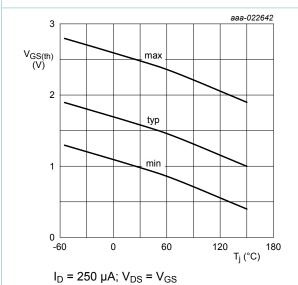
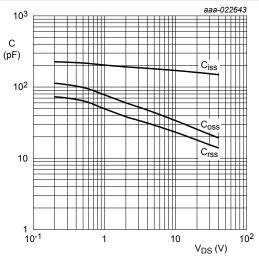


Fig. 12. Gate-source threshold voltage as a function of ambient temperature



 $f = 1 MHz; V_{GS} = 0 V$ 

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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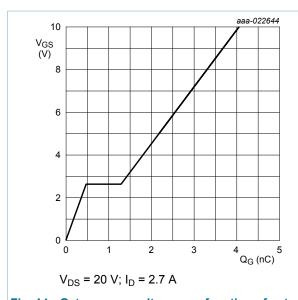


Fig. 14. Gate-source voltage as a function of gate charge; typical values

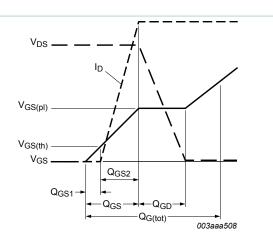


Fig. 15. MOSFET transistor: Gate charge waveform definitions

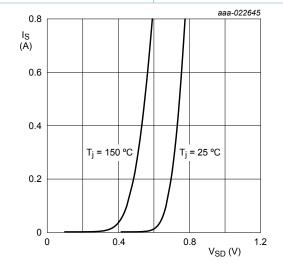
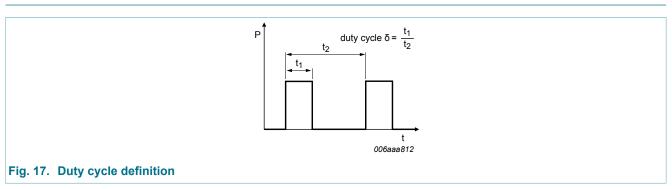


Fig. 16. Source current as a function of source-drain voltage; typical values

## 11. Test information

 $V_{GS} = 0 V$ 



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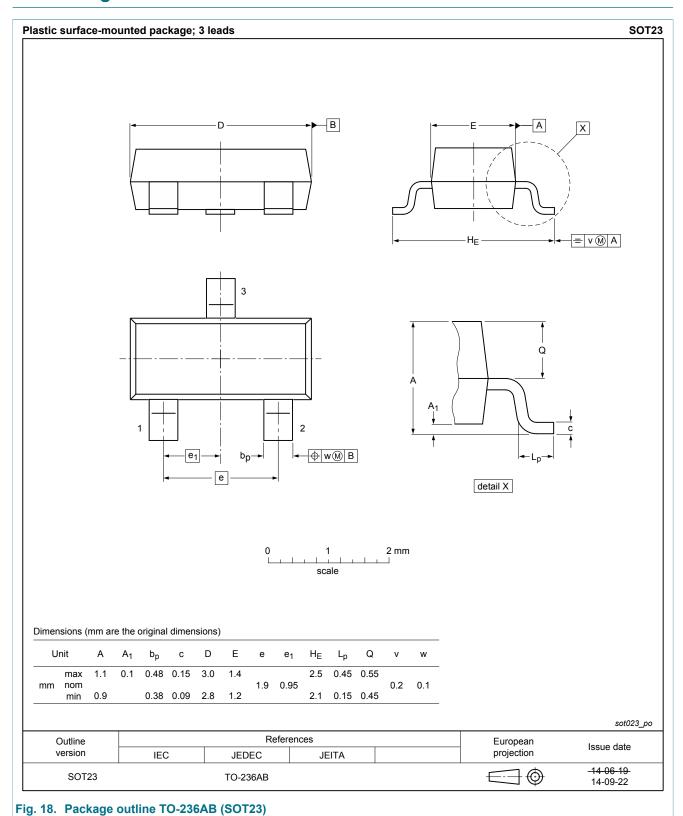
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## 11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

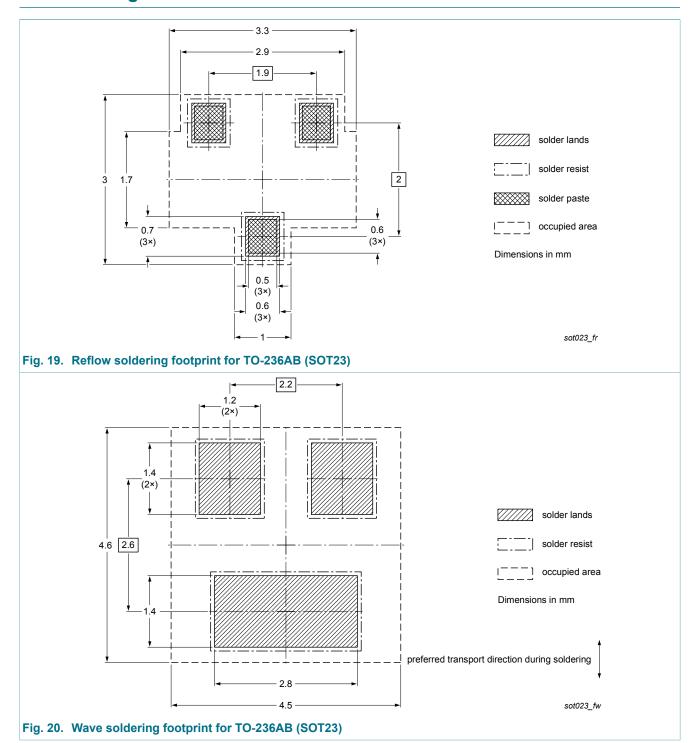
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# 12. Package outline



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## 13. Soldering



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# 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV65ENEA v.1	20160428	Product data sheet	-	-

#### 40 V, N-channel Trench MOSFET

### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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